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Vacuum, Surfaces, & Films

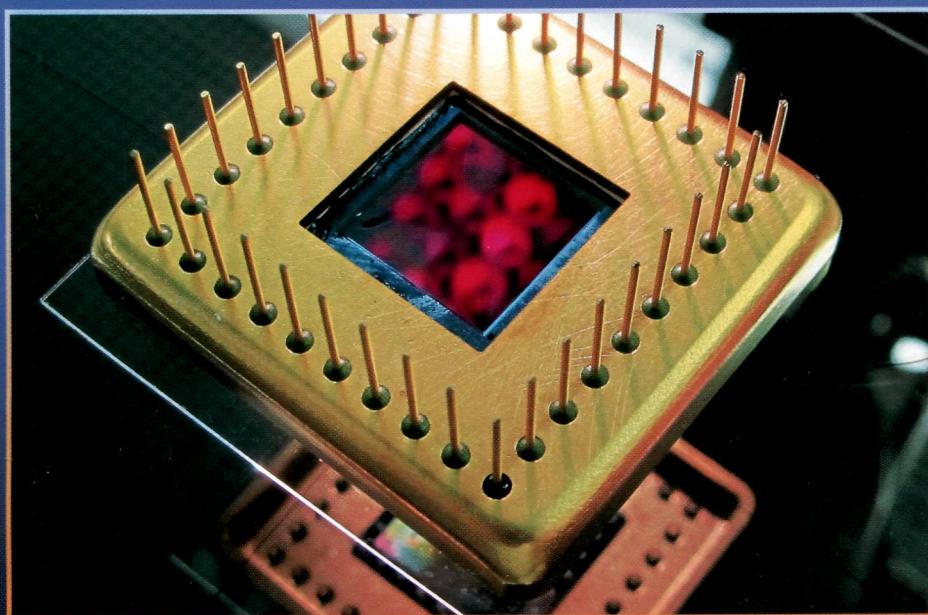


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Special Issue on Atomic Layer Deposition



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Vacuum, Surfaces, and Films

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Information for Contributors A15

Letters

Interface layer in hafnia/Si films as a function of ALD cycles

Pierre-Giovanni Mani-Gonzalez, Milton-Oswaldo Vazquez-Lepe, Francisco Espinosa-Magaña,
and Alberto Herrera-Gomez 010601

Plasma Science and Technology

Modeling of inductively coupled plasma Ar/Cl₂/N₂ plasma discharge: Effect of N₂ on the plasma properties

Romain Chanson, Ahmed Rhallabi, Marie Claude Fernandez, Christophe Cardinaud,
and Jean Pierre Landesman 011301

Can surface cracks and unipolar arcs explain breakdown and gradient limits?

Zeke Insepov and Jim Norem 011302

Reorganization of graphite surfaces into carbon micro- and nanoparticles under high flux hydrogen plasma bombardment

Kirill Bystrov, Lenze van der Vegt, Gregory De Temmerman, Cécile Arnas, and Laurent Marot 011303

Thin Films

Low emissivity high-temperature tantalum thin film coatings for silicon devices

Veronika Rinnerbauer, Jay J. Senkovich, John D. Joannopoulos, Marin Soljačić, Ivan Celanovic,
Robert R. Harl, and Bridget R. Rogers 011501

(Continued)

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Effects of the gas ambient in thermal activation of Mg-doped p-GaN on Hall effect and photoluminescence	Wei Lu, David Aplin, Arthur R. Clawson, and Paul K. L. Yu	011502
Influence of inert gases on the reactive high power pulsed magnetron sputtering process of carbon-nitride thin films	Susann Schmidt, Zsolt Czigány, Grzegorz Greczynski, Jens Jensen, and Lars Hultman.....	011503
Photoluminescence characterization of polythiophene films incorporated with highly functional molecules such as metallophthalocyanine	Hiroaki Kobe, Kazumasa Ohnaka, Hitoshi Kato, Susumu Takemura, Kazuhiro Shimada, Tomoyasu Hiramatsu, and Kazunori Matsui	011504

Brief Reports and Comments

Direct comparison of spectroscopic data with cluster calculations of plutonium dioxide and uranium dioxide	
---	--

J. G. Tobin, S.-W. Yu, B. W. Chung, M. V. Ryzhkov, and A. Mirmelstein	013001
---	--------

Shop Notes

Magnetically coupled ultrahigh vacuum manipulator with a sample grabber	
--	--

Seong Heon Kim and Alex de Lozanne	013201
--	--------

Special Issue: Atomic Layer Deposition (ALD)

Aluminum-doped zinc oxide formed by atomic layer deposition for use as anodes in organic light emitting diodes	
---	--

Su Cheol Gong, Yong-June Choi, Hyuncheol Kim, Chang-Sun Park, Hyung-Ho Park, Ji Geun Jang, Ho Jung Chang, and Geun Young Yeom	01A101
---	--------

Atomic layer deposition of Ti-HfO₂ dielectrics	
--	--

Matthew Werner, Peter J. King, Sarah Hindley, Simon Romani, Sean Mather, Paul R. Chalker, Paul A. Williams, and Jakob A. van den Berg	01A102
---	--------

Atomically precise surface engineering of silicon CCDs for enhanced UV quantum efficiency	
--	--

Frank Greer, Erika Hamden, Blake C. Jacquot, Michael E. Hoenk, Todd J. Jones, Matthew R. Dickie, Steve P. Monacos, and Shouleh Nikzad.....	01A103
--	--------

Height distribution of atomic force microscopy images as a tool for atomic layer deposition characterization	
---	--

Krzysztof Kolanek, Massimo Tallarida, and Dieter Schmeisser.....	01A104
--	--------

X-ray photoelectron spectroscopy study on the chemistry involved in tin oxide film growth during chemical vapor deposition processes	
---	--

Gilbère J. A. Mannie, Gijsbert Gerritsen, Hendrikus C. L. Abbenhuis, Joop van Deelen, J. W. (Hans) Niemantsverdriet, and Peter C. Thüne	01A105
---	--------

Substrate-biasing during plasma-assisted atomic layer deposition to tailor metal-oxide thin film growth	
--	--

H. B. Profijt, M. C. M. van de Sanden, and W. M. M. Kessels	01A106
---	--------

Ion conduction in nanoscale yttria-stabilized zirconia fabricated by atomic layer deposition with various doping rates	
---	--

Kyung Sik Son, Kiho Bae, Jun Woo Kim, Jeong Suk Ha, and Joon Hyung Shim	01A107
---	--------

On the kinetics of spatial atomic layer deposition	
---	--

Paul Poodt, Joep van Lieshout, Andrea Illiberi, Raymond Knaapen, Fred Roozeboom, and Almie van Asten	01A108
--	--------

Atomic layer deposition of Al-doped ZnO thin films	
---	--

Tommi Tynell, Hisao Yamauchi, Maarit Karppinen, Ryuji Okazaki, and Ichiro Terasaki	01A109
--	--------

(Continued)

Low temperature deposition of Ga_2O_3 thin films using trimethylgallium and oxygen plasma	01A110
Inci Donmez, Cagla Ozgit-Akgun, and Necmi Biyikli	
Excitation of radiative polaritons by polarized broadband infrared radiation in thin oxide films deposited by atomic layer deposition	01A111
Anita J. Vincent-Johnson, Andrew E. Masters, Xiaofeng Hu, and Giovanna Scarel	
Chemistry of $\text{Cu}(\text{acac})_2$ on $\text{Ni}(110)$ and $\text{Cu}(110)$ surfaces: Implications for atomic layer deposition processes	01A112
Qiang Ma and Francisco Zaera	
Combining dynamic and static depth profiling in low energy ion scattering	01A113
Rik ter Veen, Michael Fartmann, Reinhard Kersting, and Birgit Hagenhoff	
Crystal AlN deposited at low temperature by magnetic field enhanced plasma assisted atomic layer deposition	01A114
Wenwen Lei and Qiang Chen	
Hf_xZr_{1-x}O₂ compositional control using co-injection atomic layer deposition	01A115
Steven Consiglio, Kandabara Tapiiy, Robert D. Clark, Genji Nakamura, Cory S. Wajda, and Gert J. Leusink	
Atomic layer deposition of anatase TiO_2 on porous electrodes for dye-sensitized solar cells	01A116
Ingo Dirnstorfer, Hannes Mähne, Thomas Mikolajick, Martin Knaut, Matthias Albert, and Kristina Dubnack	
Effect of the amido Ti precursors on the atomic layer deposition of TiN with NH₃	01A117
Gihee Cho and Shi-Woo Rhee	
Atomic layer deposition of epitaxial TiO_2 II on c-sapphire	01A118
Aivar Tarre, Kristel Möldre, Ahti Niilisk, Hugo Mändar, Jaan Aarik, and Arnold Rosental	
Structural properties of as deposited and annealed ZrO_2 influenced by atomic layer deposition, substrate, and doping	01A119
Wenke Weinreich, Lutz Wilde, Johannes Müller, Jonas Sundqvist, Elke Erben, Johannes Heitmann, Martin Lemberger, and Anton J. Bauer	
Atomic layer deposition of Ga-doped ZnO transparent conducting oxide substrates for CdTe-based photovoltaics	01A120
Paul R. Chalker, Paul A. Marshall, Simon Romani, Joseph W. Roberts, Stuart J. C. Irvine, Daniel A. Lamb, Andrew J. Clayton, and Paul A. Williams	
Copper deposition on TiO_2 from copper(II)hexafluoroacetylacetone	01A121
David G. Rayner, James S. Mulley, and Roger A. Bennett	
Evaluating Al_2O_3 gas diffusion barriers grown directly on Ca films using atomic layer deposition techniques	01A122
Jacob A. Bertrand and Steven M. George	
TEMAZ/O₃ atomic layer deposition process with doubled growth rate and optimized interface properties in metal–insulator–metal capacitors	01A123
Wenke Weinreich, Tina Tauchnitz, Patrick Polakowski, Maximilian Drescher, Stefan Riedel, Jonas Sundqvist, Konrad Seidel, Mahdi Shirazi, Simon D. Elliott, Susanne Ohsiek, Elke Erben, and Bernhard Trui	
Effect of <i>in situ</i> hydrogen plasma treatment on zinc oxide grown using low temperature atomic layer deposition	01A124
Tae-Hoon Jung, Jin-Seong Park, Dong-Ho Kim, Yongsoo Jeong, Sung-Gyu Park, and Jung-Dae Kwon	
Atomic layer deposition of aluminum-doped zinc oxide films for the light harvesting enhancement of a nanostructured silicon solar cell	01A125
Sheng-Hui Chen, Shih-Hao Chan, Chun-Ko Chen, Shao-Ze Tseng, Chieh-Hsiang Hsu, and Wen-Hao Cho	
Probing the properties of atomic layer deposited ZrO_2 films on p-Germanium substrates	01A126
Ariadne P. Kerasidou, Martha A. Botzakaki, Nikolaos Xanthopoulos, Stella Kennou, Spyridon Ladas, Stavroula N. Georgia, and Christoforos A. Krontiras	

(Continued)

Electrical characterization of atomic-layer-deposited hafnium oxide films from hafnium tetrakis(dimethylamide) and water/ozone: Effects of growth temperature, oxygen source, and postdeposition annealing

Hector García, Helena Castán, Salvador Dueñas, Luis Bailón, Francesca Campabadal, Oihane Beldarrain, Miguel Zabala, Mireia Bargallo González, and Joan Marc Raffi

01A127

Blistering of atomic layer deposition Al_2O_3 layers grown on silicon and its effect on metal–insulator–semiconductor structures

Oihane Beldarrain, Marta Duch, Miguel Zabala, Joan Marc Raffi, Mireia Bargalló González, and Francesca Campabadal

01A128

Low-temperature atomic layer deposition of Al_2O_3 on blown polyethylene films with plasma-treated surfaces

Gyeong Beom Lee, Kyung Sik Son, Suk Won Park, Joon Hyung Shim, and Byoung-Ho Choi

01A129

New approach toward transparent and conductive ZnO by atomic layer deposition: Hydrogen plasma doping

Matthew A. Thomas, Johnathan C. Armstrong, and Jingbiao Cui

01A130

Atomic layer deposition of zinc indium sulfide films: Mechanistic studies and evidence of surface exchange reactions and diffusion processes

Pascal Genevée, Frédérique Donsanti, Nathanaelle Schneider, and Daniel Lincot

01A131

Physical and electrical characteristics of atomic-layer deposition- HfO_2 films deposited on Si substrates having different silanol Si-OH densities

Joel Molina, Carlos Zuniga, Wilfrido Calleja, Pedro Rosales, Alfonso Torres, and Alberto Herrera-Gomez

01A132

Preparation and phase structures of $\text{Zn}-\text{Ti}-\text{O}$ ternary compounds by atomic layer deposition

Xu Qian, Mo-Yun Gao, Yan-Qiang Cao, Bing-Lei Guo, and Ai-Dong Li

01A133

Characterization of atomic layer deposition HfO_2 , Al_2O_3 , and plasma-enhanced chemical vapor deposition Si_3N_4 as metal–insulator–metal capacitor dielectric for GaAs HBT technology

Jiro Yota, Hong Shen, and Ravi Ramanathan

01A134

Atomic layer deposition of Al_2O_3 and $\text{Al}_x\text{Ti}_{1-x}\text{O}_y$ thin films on N_2O plasma pretreated carbon materials

Andrey M. Markeev, Anna G. Chernikova, Anastasya A. Chouprik, Sergey A. Zaitsev, Dmitry V. Ovchinnikov, Holger Althues, and Susanne Dörfler

01A135

Epitaxial strontium titanate films grown by atomic layer deposition on SrTiO_3 -buffered Si(001) substrates

Martin D. McDaniel, Agham Posadas, Thong Q. Ngo, Ajit Dhamdhare, David J. Smith, Alexander A. Demkov, and John G. Ekerdt

01A136

Low-temperature ($\leq 200^\circ\text{C}$) plasma enhanced atomic layer deposition of dense titanium nitride thin films

Nigamananda Samal, Hui Du, Russell Luberooff, Krishna Chetry, Randhir Bubber, Alan Hayes, and Adrian Devasahayam

01A137

Atomic layer deposition of zinc sulfide with $\text{Zn}(\text{TMHD})_2$

Andrew Short, Leila Jewell, Sage Doshay, Carena Church, Trevor Keiber, Frank Bridges, Sue Carter, and Glenn Alers

01A138

Atomic layer deposition onto carbon fiber: From single layer deposition via multilayer structure to metal oxide microtubes

Stefan Knohl, Amit Kumar Roy, Werner A. Goedel, Steffen Schulze, and Michael Hietschold

01A139

Gallium nitride MIS-HEMT using atomic layer deposited Al_2O_3 as gate dielectric

Richard Lossy, Hassan Gargouri, Michael Arens, and Joachim Würfl

01A140

Comprehensive comparison of structural, electrical, and reliability characteristics of HfO_2 gate dielectric with H_2O or O_3 oxidant

Yi-Lung Cheng, You-Ling Chang, Cheng-Yang Hsieh, and Jian-Run Lin

01A141

Comparison between ZnO films grown by plasma-assisted atomic layer deposition using H_2O plasma and O_2 plasma as oxidant

Yumi Kawamura, Nozomu Hattori, Naomasa Miyatake, and Yukiharu Uraoka

01A142

(Continued)

Interfacial chemistry of hydrofluoric acid-treated $In_{0.53}Ga_{0.47}As(100)$ during atomic layer deposition of aluminum oxide

Bernal Granados-Alpizar, Fee Li Lie, and Anthony J. Muscat 01A143

Atomic layer deposition of ZnO on Cu-nanoclusters for methanol synthesis

Ziyu Zhang, Matthew Patterson, Maoming Ren, Ying Wang, John C. Flake, Phillip T. Sprunger, and Richard L. Kurtz 01A144

Atomic layer deposition of cobalt oxide thin films using cyclopentadienylcobalt dicarbonyl and ozone at low temperatures

Byeol Han, Kyu Ha Choi, Jae Min Park, Jung Woo Park, Jongwan Jung, and Won-Jun Lee 01A145

Electrical conductivity and photoresistance of atomic layer deposited Al-doped ZnO films

Rajeh M. Mundle, Hampton S. Terry, Kevin Santiago, Dante Shaw, Messaoud Bahoura, Aswini K. Pradhan, Kiran Dasari, and Ratnakar Palai 01A146

Wetting transitions of polymers via thermal and plasma enhanced atomic layer depositions

Amit K. Roy, Davy Deduytsche, and Christophe Detavernier 01A147

Characterization of low temperature deposited atomic layer deposition TiO₂ for MEMS applications

Yujian Huang, Gregory Pandraud, and Pasqualina M. Sarro 01A148

Stability and annealing of alucones and alucone alloys

Lilit Ghazaryan, Ernst-Bernhard Kley, Andreas Tünnermann, and Adriana Viorica Szeghalmi 01A149

CUMULATIVE AUTHOR INDEX..... A21

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